



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

MCH6431 — N-Channel Silicon MOSFET — General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)} = 42\text{m}\Omega$ (typ.)
- 4V drive
- Halogen free compliance
- Protection diode in

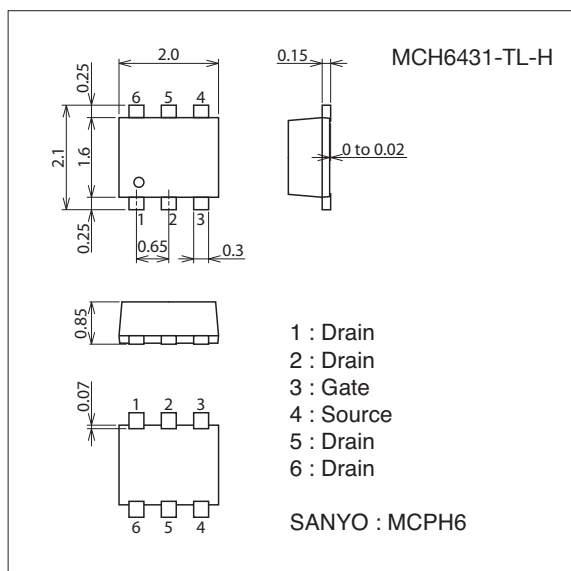
Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	20	A
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² × 0.8mm)	1.5	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Package Dimensions

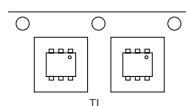
unit : mm (typ)
7022A-009



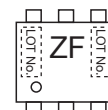
Product & Package Information

- Package : MCPH6
- JEITA, JEDEC : SC-88, SC-70-6, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

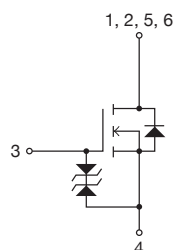
Packing Type : TL



Marking



Electrical Connection

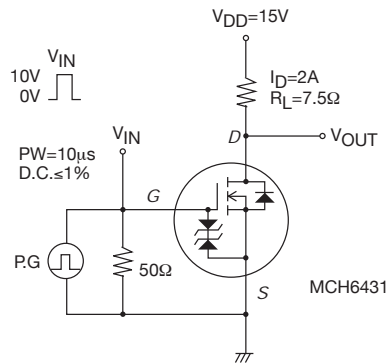


MCH6431

Electrical Characteristics at $T_a=25^\circ\text{C}$

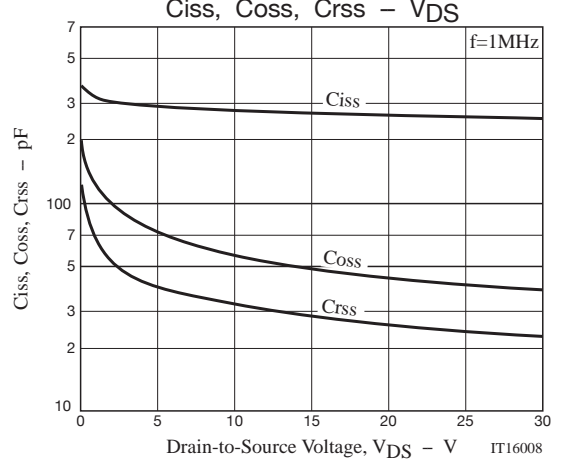
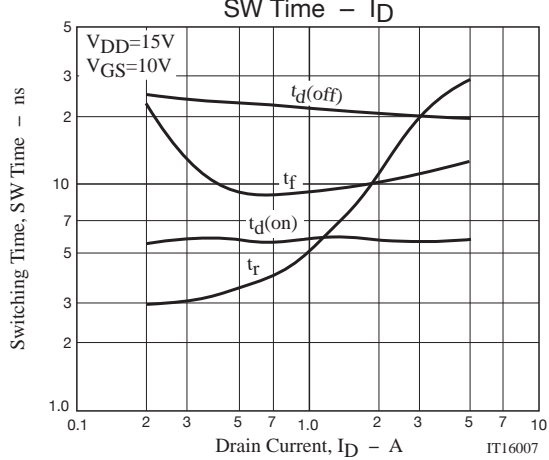
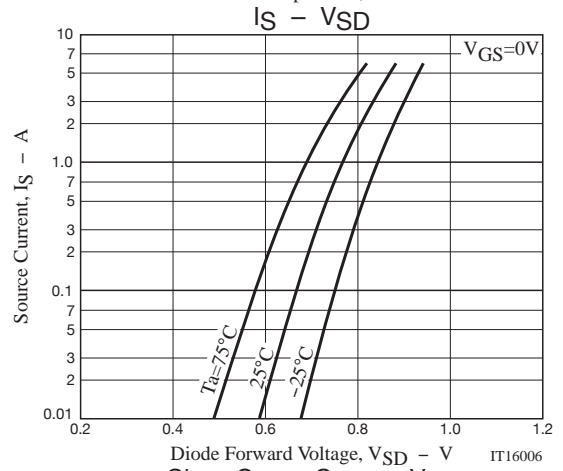
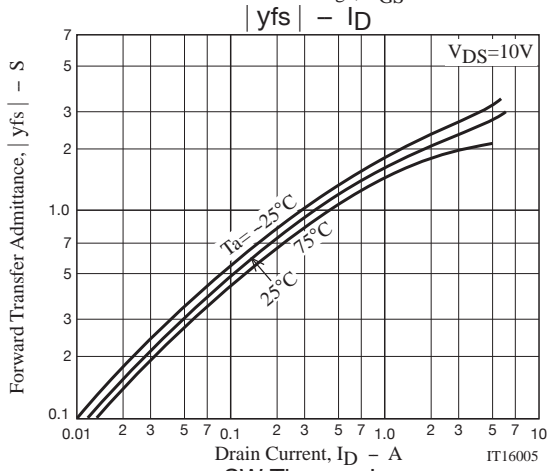
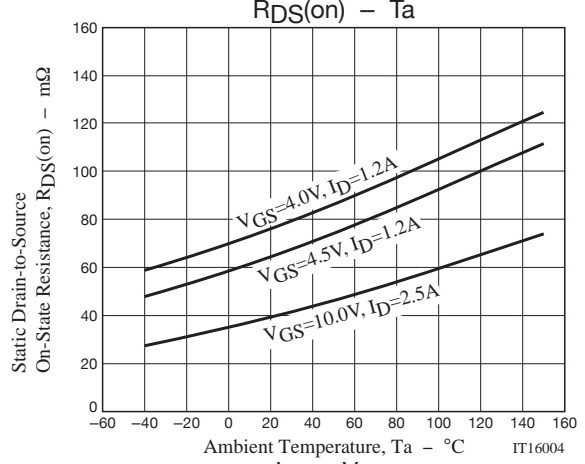
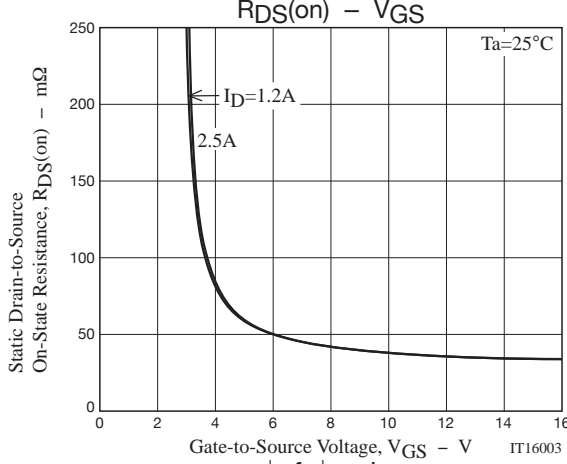
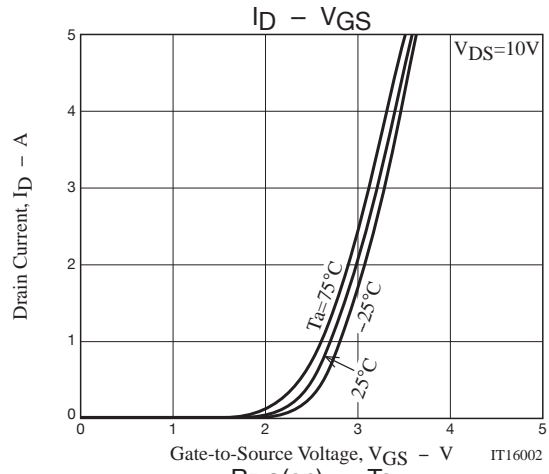
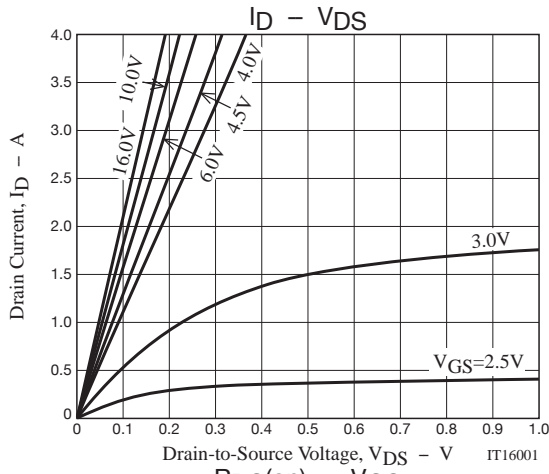
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}, V_{GS}=0\text{V}$	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16\text{V}, V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}, I_D=2.5\text{A}$		2.2		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=2.5\text{A}, V_{GS}=10\text{V}$		42	55	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=1.2\text{A}, V_{GS}=4.5\text{V}$		65	91	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D=1.2\text{A}, V_{GS}=4\text{V}$		78	109	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10\text{V}, f=1\text{MHz}$		280		pF
Output Capacitance	C_{oss}			60		pF
Reverse Transfer Capacitance	C_{rss}			30		pF
Turn-ON Delay Time	$t_{d(on)}$		See specified Test Circuit.		5.7	
Rise Time	t_r			11		ns
Turn-OFF Delay Time	$t_{d(off)}$			21		ns
Fall Time	t_f			10		ns
Total Gate Charge	Q_g	$V_{DS}=15\text{V}, V_{GS}=10\text{V}, I_D=5\text{A}$			5.6	
Gate-to-Source Charge	Q_{gs}			1.2		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			0.8		nC
Diode Forward Voltage	V_{SD}	$I_S=5\text{A}, V_{GS}=0\text{V}$		0.85	1.2	V

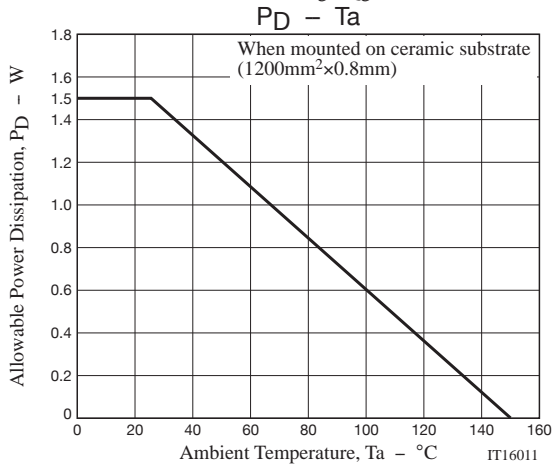
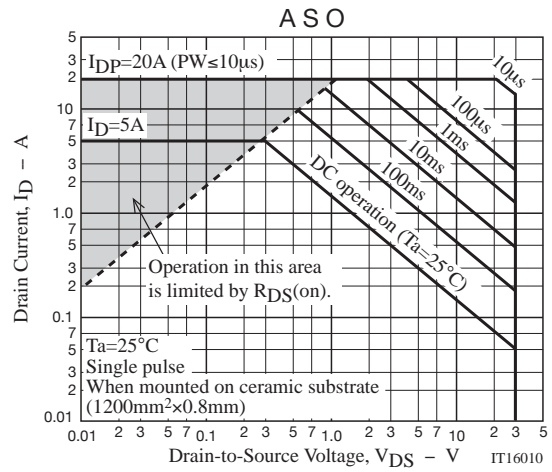
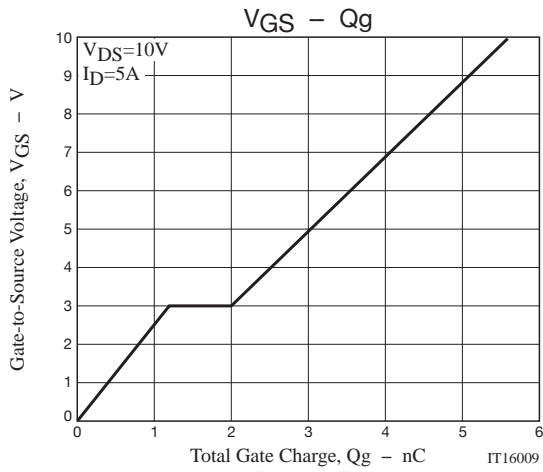
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
MCH6431-TL-H	MCPH6	3,000pcs./reel	Pb Free and Halogen Free



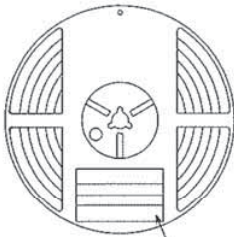


Taping Specification
MCH6431-TL-H

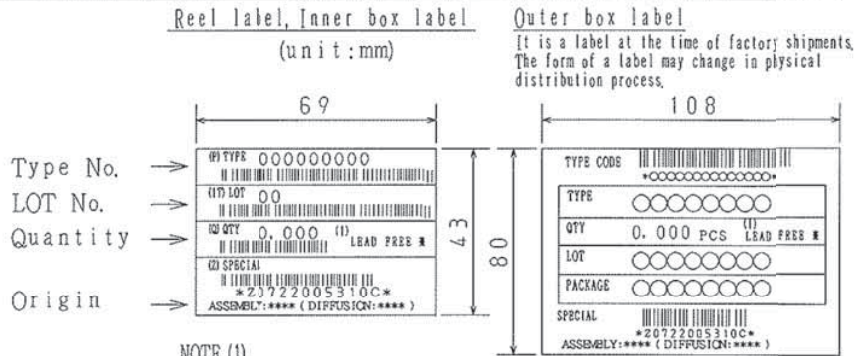
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (tcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
MCPH6	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label



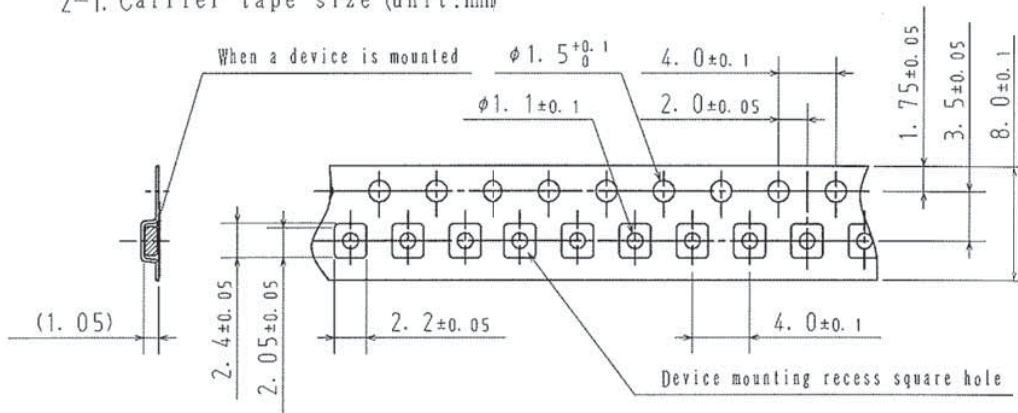
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

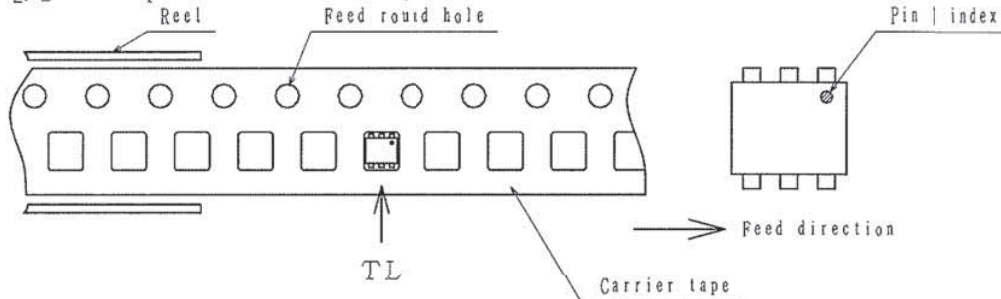
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



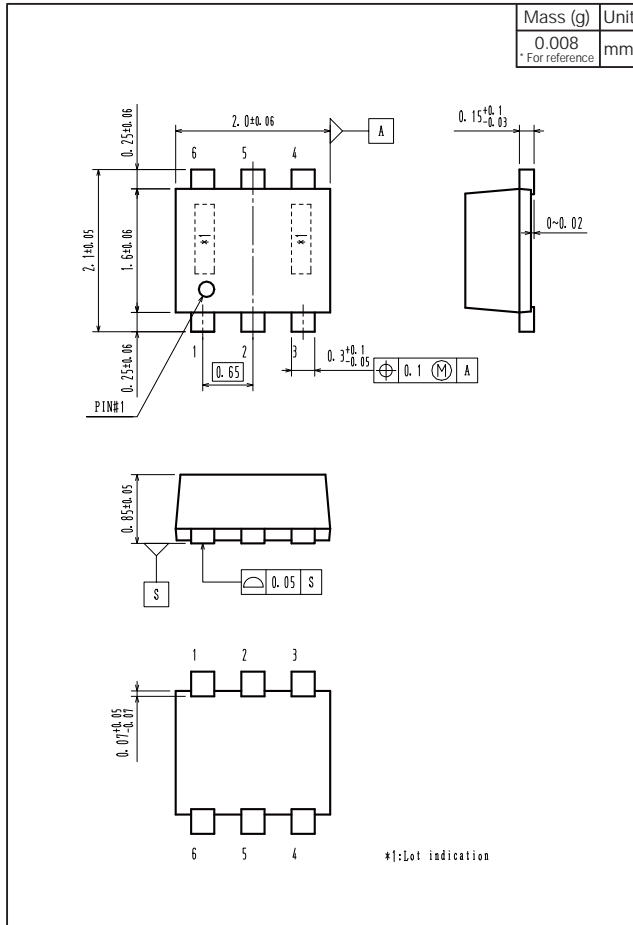
2-2. Device placement direction



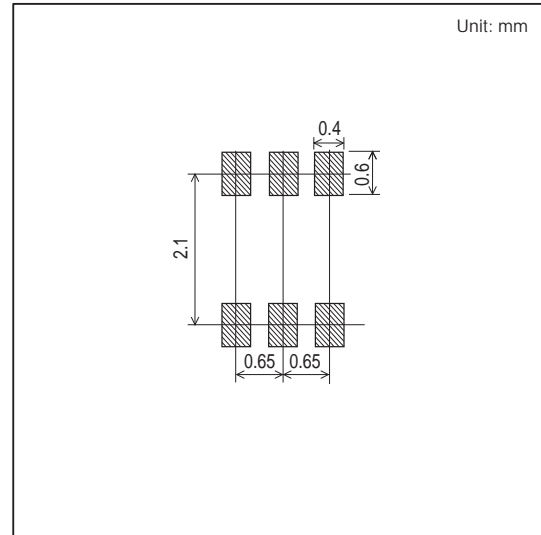
Those with pin 1 index on the feed hole side.....TL

MCH6431

Outline Drawing MCH6431-TL-H



Land Pattern Example



Note on usage : Since the MCH6431 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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